
HRU0302A

Silicon Schottky Barrier Diode for Rectifying

HITACHI

ADE-208-235E(Z)

Rev 5

June 1996

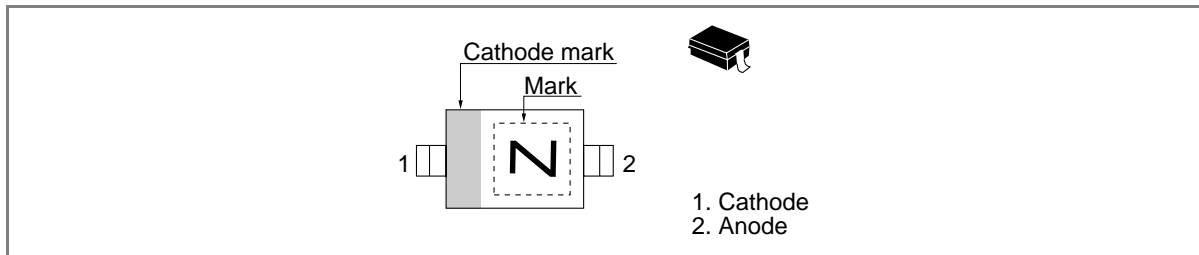
Features

- Low forward voltage drop and suitable for high efficiency forward current.
- Ultra small Resin Package (URP) is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HRU0302A	Z	URP

Outline



HRU0302A

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Repetitive peak reverse voltage	VRRM*1	20	V
Average rectified current	IO*2	300	mA
Non-Repetitive peak forward surge current	IFSM*3	3	A
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55 to +125	°C

Notes 1. See Fig.4

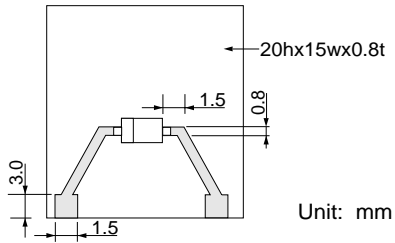
Notes 2. See Fig.5

sec half sine wave 1 pulse

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	VF	0.4	0.4	0.4	V	IF = 300 mA
Reverse current	IR	100	100	100	μA	VR = 20V
Capacitance	C	70	70	70	pF	VR = 0V, f = 1 MHz
Thermal resistance	Rth(j-a)	440	440	440	°C/W	Polyimide substrate*1

Notes 1. Polyimide PCB



Main Characteristic

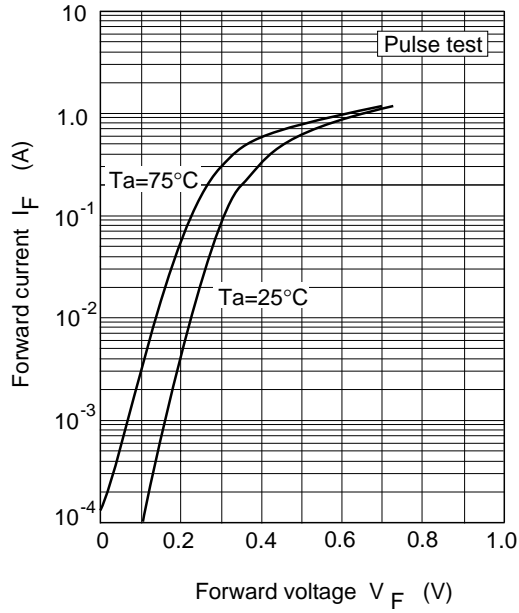


Fig.1 Forward current Vs. Forward voltage

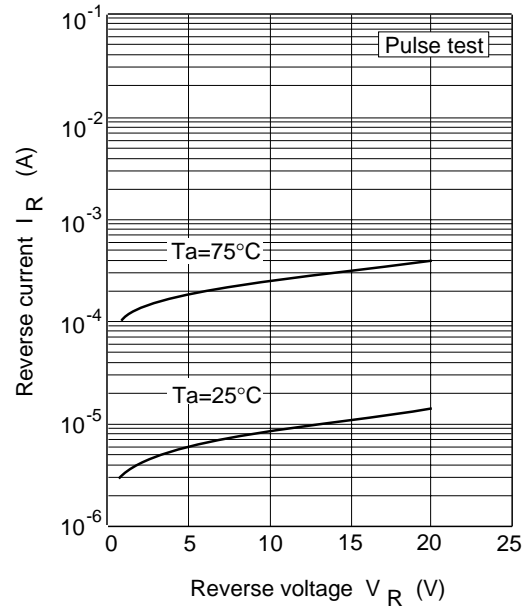


Fig.2 Reverse current Vs. Reverse voltage

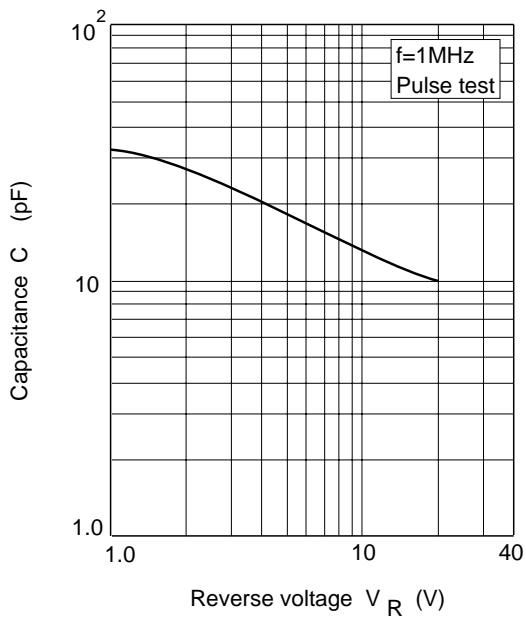


Fig.3 Capacitance Vs. Reverse voltage

Main Characteristic

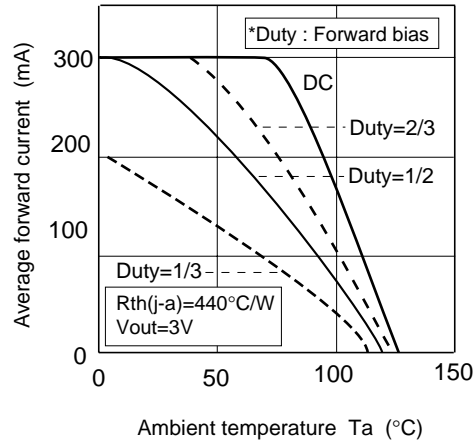


Fig.4 Average forward current Vs. Ambient temperature

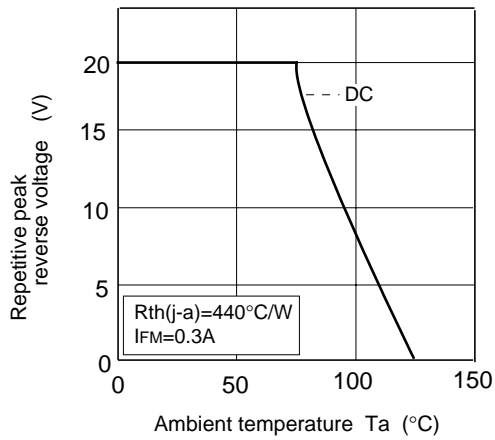


Fig.5 Repetitive peak reverse voltage Vs. Ambient temperature

Package Dimensions

Unit : mm

